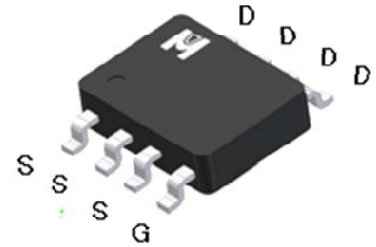
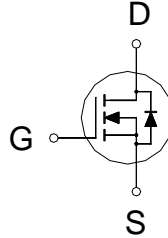


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	200V
$R_{DS(on)}$ (MAX.)	0.5 Ω
I_D	1.6A



UIS, 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 30	V
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	1.6	A
	$T_A = 100\text{ }^\circ\text{C}$		1	
Pulsed Drain Current ¹		I_{DM}	6.4	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	2.5	W
	$T_A = 100\text{ }^\circ\text{C}$		1	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		25	$^\circ\text{C} / \text{W}$
Junction-to-Ambient ³	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³50 $^\circ\text{C} / \text{W}$ when mounted on a 1 in² pad of 2 oz copper.



ELECTRICAL CHARACTERISTICS ($T_c = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	3.0	4.0	5.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 30V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 160V, V_{GS} = 0V$			1	μA
		$V_{DS} = 130V, V_{GS} = 0V, T_J = 125\text{ }^\circ\text{C}$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	1.6			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.8A$		0.4	0.5	Ω
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 0.8A$		2		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		803		pF
Output Capacitance	C_{oss}			19		
Reverse Transfer Capacitance	C_{rss}			16		
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = 100V, V_{GS} = 10V,$ $I_D = 0.8A$		21.3		nC
Gate-Source Charge ^{1,2}	Q_{gs}			2.9		
Gate-Drain Charge ^{1,2}	Q_{gd}			6		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 100V,$ $I_D = 0.5A, V_{GS} = 10V, R_{GS} = 6\Omega$		20		nS
Rise Time ^{1,2}	t_r			60		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			20		
Fall Time ^{1,2}	t_f			50		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25\text{ }^\circ\text{C}$)						
Continuous Current	I_S				1.6	A
Pulsed Current ³	I_{SM}				6.4	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.5	V

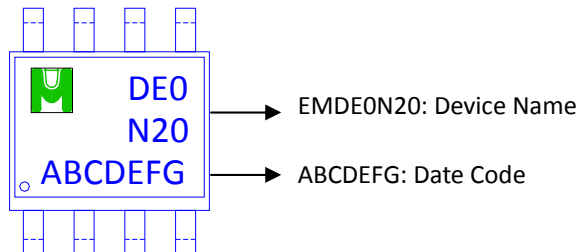
¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

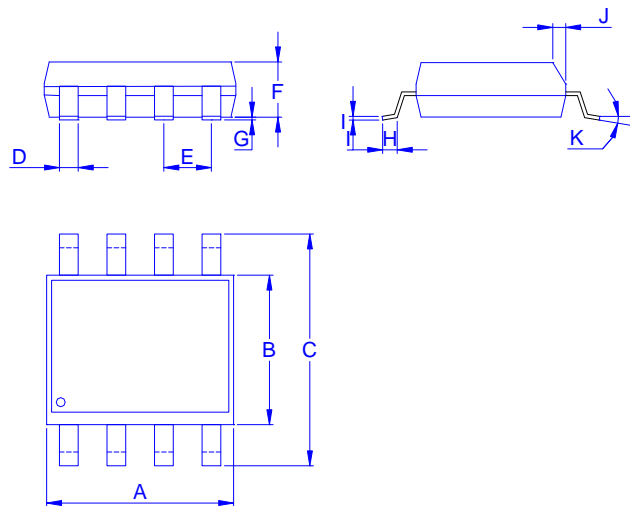
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMDE0N20G for SOP-8



Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
in.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°



TYPICAL CHARACTERISTICS

